To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SK494

Silicon N-Channel Junction FET

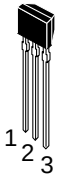
ADE-208-1173 (Z)
1st. Edition
Mar. 2001

Application

Low frequency / High frequency amplifier

Outline

SPAK



1. Drain
2. Gate
3. Source

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	22	V
Gate to source voltage	V_{GSO}	–22	V
Drain current	I_D	100	mA
Gate current	I_G	10	mA
Channel power dissipation	Pch	300	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

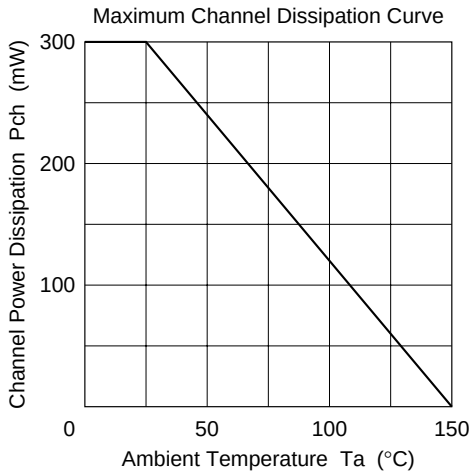
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Gate to source breakdown voltage	$V_{(BR)GSS}$	–22	—	—	V	I_G = –10 µA, V_{DS} = 0
Gate cutoff current	I_{GSS}	—	—	–10	nA	V_{GS} = –15 V, V_{DS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	—	—	–2.5	V	V_{DS} = 5 V, I_D = 10 µA
Drain current	I_{DSS}*[1]	6	—	40	mA	V_{DS} = 5 V, V_{GS} = 0, Pulse test
Forward transfer admittance	$\|y_{fs}\|$	20	—	—	mS	V_{DS} = 5 V, I_D = 10 mA, f = 1 kHz
Input capacitance	Ciss	—	9.0	11.0	pF	V_{DS} = 5 V, V_{GS} = 0, f = 1 MHz
Reverse transfer capacitance	Crss	—	2.8	4.0	pF	V_{DS} = 5 V, V_{GS} = 0, f = 1 MHz
Noise figure	NF	—	0.5	3.0	dB	V_{DS} = 5 V, I_D = 1 mA, f = 1 kHz, Rg = 1 kΩ

Note: 1. The 2SK494 is grouped by I_{DSS} as follows.

Grade	B	C	D	E
I_{DSS}	6 to 14	12 to 22	18 to 30	26 to 40

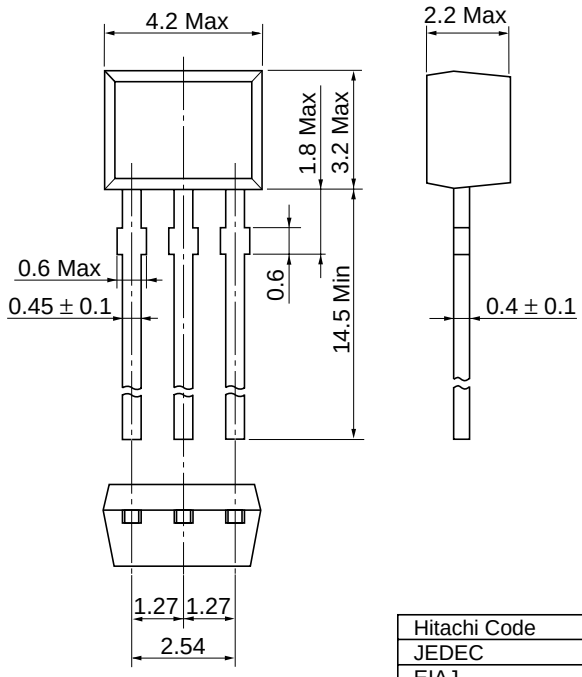
See character curves 2SK435.

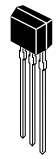

Maximum Channel Dissipation Curve
Channel Power Dissipation Pch (mW)
300
200
100
0
50
100
150
Ambient Temperature Ta (°C)

Package Dimensions

As of January, 2001

Unit: mm





Hitachi Code	SPAK
JEDEC	—
EIAJ	—
Mass (reference value)	0.10 g

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